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Appl. No. 10/801,475
Reply to Office Action of August 28, 2006Attorney Docket No. 2003-1410 / 24061.193
Customer No. 42717**Amendments to the Specification**

Please replace paragraph [0022] with the following amended paragraph:

[0022] Referring now to Fig. 6, shown therein is another top view of a simplified metallurgy layer 80 of a semiconductor device according to one embodiment of the present disclosure. In this embodiment, dummy structures 56, 58 and 60 are thermally connected together by lines 62 and 64. In fact, all the dummy structures located on side A of a conductive line 72 have been connected together. Likewise, all the dummy structures located on side B of a conductive line 72 have been connected together. Here, one or more lines 66 are utilized to ~~connected~~ thermally connect dummy structures on side A of the conductive line 72 to a seal ring 68. Likewise, one or more lines 74 are utilized to ~~connected~~ thermally connect dummy structures on side B of the conductive line 72 to the seal ring 68. Through one or more vias 70, the seal ring 68 of the metallurgy layer 80 may be thermally connected to the seal rings of other metallurgy layers. Accordingly, dummy structures on the metallurgy layer 80 may be thermally connected to dummy structures on other metallurgy layers. It is contemplated that not all dummy structures on side A or B of the conductive line 72 may be connected. As a result, not all dummy structures on the metallurgy layer 80 may be connected to dummy structures on other metallurgy layers. Further, each of the lines 66 and 74 may comprise a variety of shapes, materials and sizes. For example, each of them may comprise a rectangular prism, polygon, partial rectangular prism, cube, partial cube, sphere, partial sphere, pyramid, partial pyramid, cone, partial cone or other regular or irregular shapes. It is contemplated that each of the lines 66 and 74 may comprise copper, aluminum, other type of metals, or other materials suitable for heat dissipation. Further, the widths of the lines 66 and 74 may be larger than one micrometer. Alternatively, the widths of the lines 66 and 74 may be no more than one micrometer. Finally, each of the lines 66 and 74 may be identical or different.